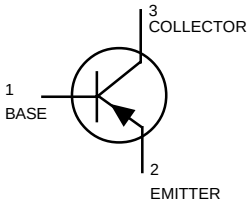
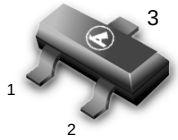
General Purpose Transistor

PNP Silicon



MMBT2907LT1
MMBT2907ALT1



CASE 318–08, STYLE 6
SOT–23 (TO–236AB)

MAXIMUM RATINGS

Rating	Symbol	Value 2907	Value 2907A	Unit
Collector–Emitter Voltage	V_{CEO}	–40	–60	Vdc
Collector–Base Voltage	V_{CBO}	–60		Vdc
Emitter–Base Voltage	V_{EBO}	–5.0		Vdc
Collector Current — Continuous	I_C	–600		mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR– 5 Board, (1) T_A = 25°C	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (2) T_A = 25°C	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J , T_{stg}	–55 to +150	°C

DEVICE MARKING

MMBT2907LT1 = M2B, MMBT2907ALT1 = 2F

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage(3)		$V_{(BR)CEO}$			Vdc
(I_C = –10 mAdc, I_B = 0)	MMBT2907		–40	—	
	MMBT2907A		–60	—	
Collector–Emitter Breakdown Voltage(I_C = –10 µAdc, I_E = 0)		$V_{(BR)CBO}$	–60	—	Vdc
Emitter–Base Breakdown Voltage(I_E = –10 µAdc, I_C = 0)		$V_{(BR)EBO}$	–5.0	—	Vdc
Collector Cutoff Current(V_{CB} = –30Vdc, $I_{BE(OFF)}$ = –0.5Vdc)		I_{CEX}	—	–50	nAdc
Collector Cutoff Current		I_{CBO}			µAdc
(V_{CB} = –50Vdc, I_E = 0)	MMBT2907		—	–0.020	
	MMBT2907A		—	–0.010	
(V_{CB} = –50Vdc, I_E = 0, T_A =125°C)	MMBT2907		—	–20	
	MMBT2907A		—	–10	
Base Current(V_{CE} = –30Vdc, $V_{EB(off)}$= –0.5Vdc)		I_B	—	–50	nAdc

1. FR–5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.
3. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

MMBT2907LT1 MMBT2907ALT1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			—
(I_C = –0.1mAdc, V_{CE} = –10 Vdc)	MMBT2907		35	—	
	MMBT2907A		75	—	
(I_C =–1.0mAdc, V_{CE} = –10 Vdc)	MMBT2907		50	—	
	MMBT2907A		100	—	
(I_C = –10 mAdc, V_{CE} = –10Vdc)	MMBT2907		75	—	
	MMBT2907A		100	—	
(I_C = –150mAdc, V_{CE} =–10 Vdc)(3)	MMBT2907		—	—	
	MMBT2907A		100	300	
(I_C = –500mAdc, V_{CE} =–10 Vdc)(3)	MMBT2907		30	—	
	MMBT2907A		50	—	
Collector–Emitter Saturation Voltage(3)		$V_{CE(sat)}$			Vdc
(I_C = –150mAdc, I_B = –15 mAdc)			—	–0.4	
(I_C = –500 mAdc, I_B = –50 mAdc)			—	–1.6	
Base–Emitter Saturation Voltage(3)		$V_{BE(sat)}$			Vdc
(I_C = –150mAdc, I_B = –15 mAdc)			—	–1.3	
(I_C = –500mAdc, I_B = –50 mAdc)			—	–2.6	
SMALL–SIGNAL CHARACTERISTICS					
Current–Gain — Bandwidth Product(3),(4) (I_C = –50mAdc, V_{CE}= –20Vdc, f = 100MHz)		f_T	200	—	MHz
Output Capacitance (V_{CB} = –10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	8.0	pF
Input Capacitance (V_{EB} = –2.0Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	30	pF
SWITCHING CHARACTERISTICS					
Turn–On Time	(V_{CC} = –30 Vdc, I_C = –150 mAdc, I_{B1} = –15 mAdc)	t_{on}	—	45	ns
Delay Time		t_d	—	10	
Rise Time		t_r	—	40	
Fall Time	(V_{CC} = –6.0 Vdc, I_C = –150 mAdc,I_{B1} = I_{B2} = 15 mAdc)	t_f	—	30	ns
Storage Time		t_s	—	80	
Turn–Off Time		t_{off}	—	100	

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
4. f_T is defined as the frequency at which $|h f_e|$ extrapolates to unity.

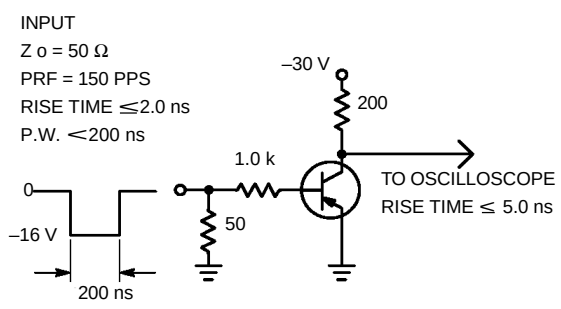


Figure 1. Delay and Rise Time Test Circuit

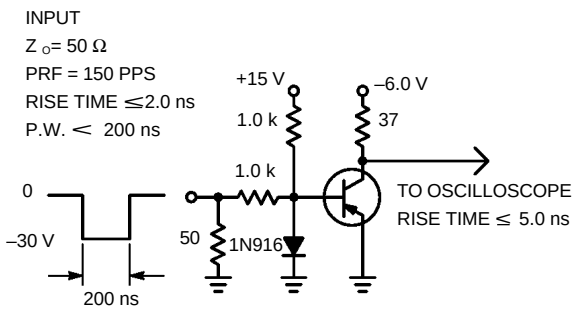


Figure 2. Storage and Fall Time Test Circuit

MMBT2907LT1 MMBT2907ALT1

TYPICAL CHARACTERISTICS

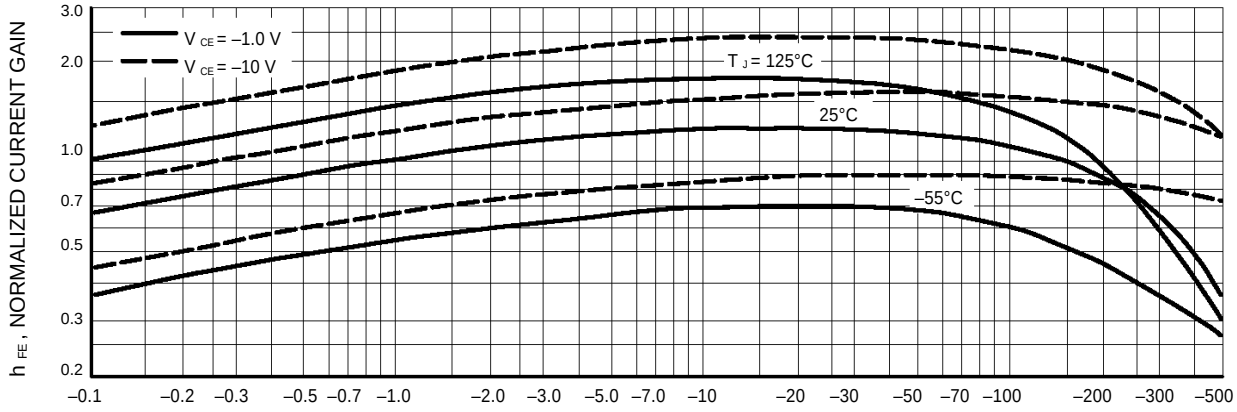


Figure 3. DC Current Gain

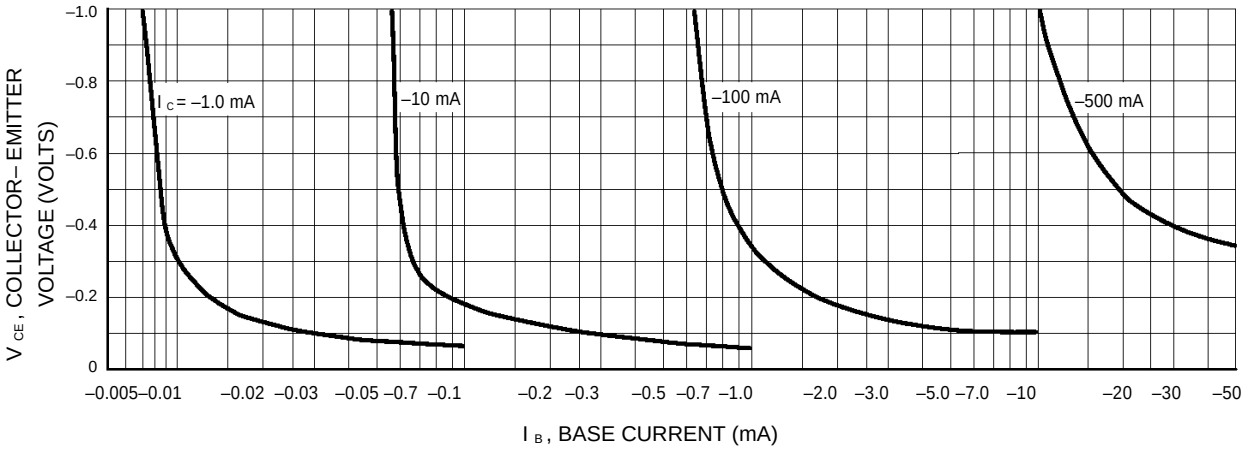


Figure 4. Collector Saturation Region

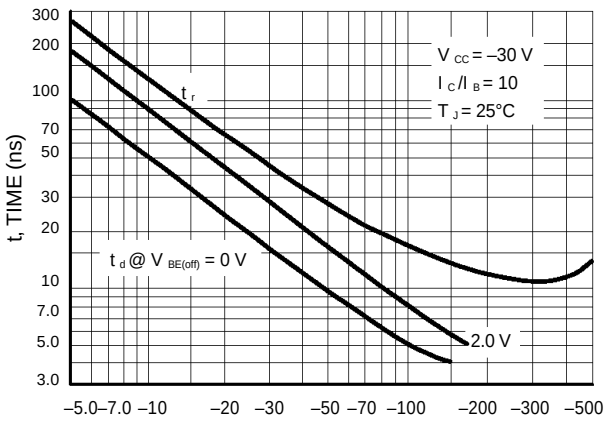


Figure 5. Turn–On Time

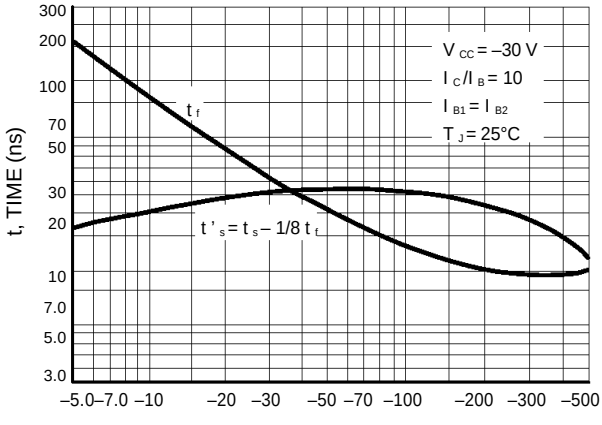


Figure 6. Turn–Off Time

TYPICAL SMALL–SIGNAL CHARACTERISTICS

NOISE FIGURE

V_{CE} = 10 Vdc, T_A = 25°C

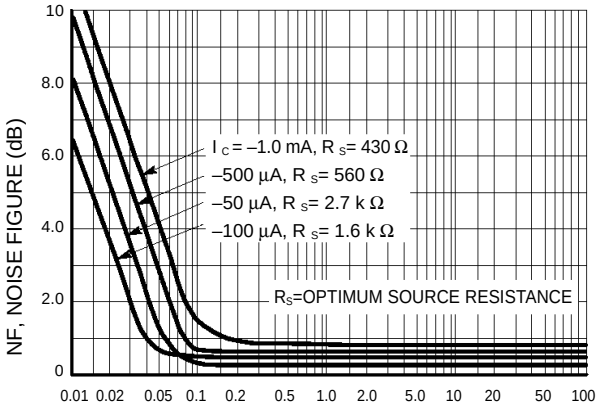


Figure 7. Frequency Effects

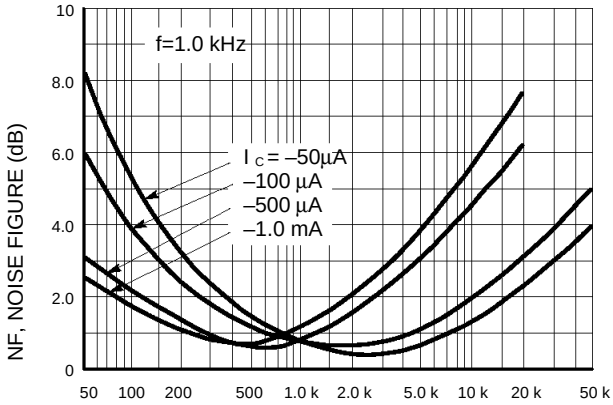


Figure 8. Source Resistance Effects

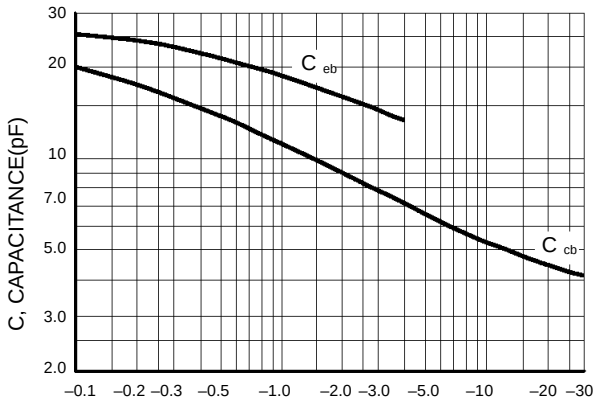


Figure 9. Capacitances

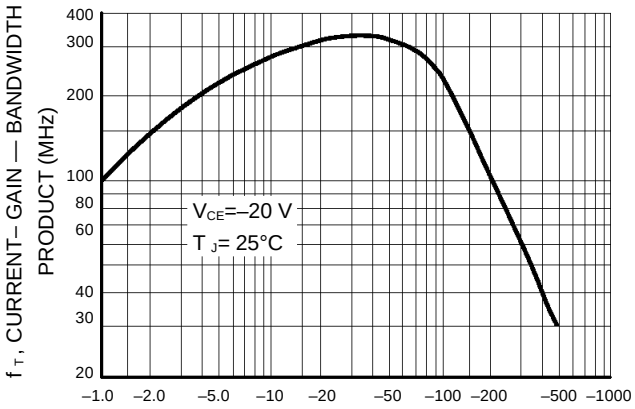


Figure 10. Current–Gain — Bandwidth Product

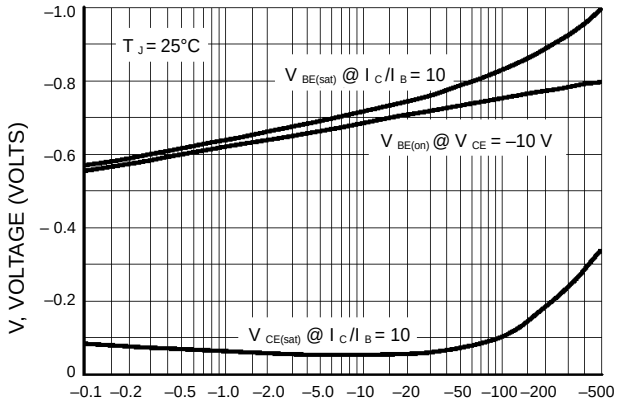


Figure 11. “On” Voltage

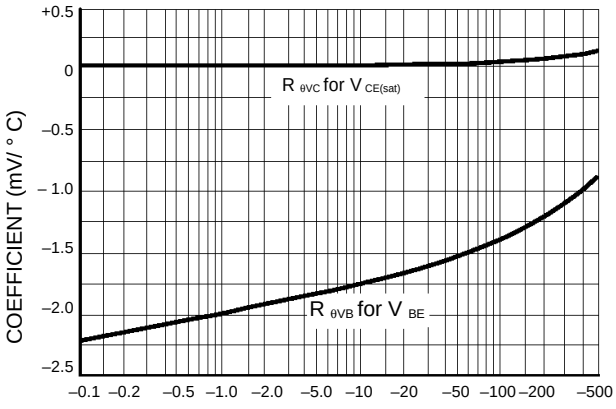


Figure 12. Temperature Coefficients